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of Montclair Newly released online in Montclair is Taste of Montclair, a free mobile app that allows residents to locate restaurants offering dining with a community and social element, and connect to their digital menu and reservations. The app was produced by VisitMunich and will be available for download in the iTunes App Store and Android Market. "This app is a community and social app that will enhance the traveling and eating experience of our fans of Montclair restaurants," said Jennifer Moravec, general manager of the Montclair Visitors Bureau. "Montclair is home to restaurants, dining and restaurants that celebrate the human connection we all value, as well as distinctive culinary experiences that are increasingly hard to find outside of our community." The app locates all of the eateries in Montclair with greater ease than other search tools, providing features such as detailed menus and a map and restaurant photo galleries. Android users may download the app from the Android Market website. iPad users can download the app from the iTunes App Store and Mac users can

1. Field of the Invention The present invention relates to a method for manufacturing an integrated circuit device and, more particularly, to a method for manufacturing an integrated circuit device in which a silicon oxide film is used as a gate insulating film of a MISFET (Metal Insulator Semiconductor Field Effect Transistor). 2. Description of the Prior Art It is known that, in an integrated circuit device, the ability of a gate insulating film is degraded as the size of a MISFET is reduced. In order to prevent this degradation of the ability of the gate insulating film, the thickness of the gate insulating film is conventionally increased. This is because the film thickness of the gate insulating film affects the transistor performance, such as threshold voltage, transconductance, etc. When the thickness of a gate insulating film is increased, however, the gate insulating film has a larger surface area and, consequently, an increase in gate capacity. In addition, the thickness of the gate insulating film has a relationship with a gate length of the MISFET and, thereby, if the gate length is increased, the ability of the gate insulating film is degraded. In other words, the gate insulating film has a limit for reducing the size of the MISFET. It is also known that, even if the size of the MISFET can be reduced, the gate insulating film has a limit for reducing the surface area thereof. This is because the gate insulating film is formed in the shape of a trench in order to reduce the size of the MISFET. However, if the surface area of the gate insulating film is reduced, the electric field applied between the polysilicon gate electrode and the gate insulating film is reduced, and an increase in the gate capacity would be caused. In other words, the thickness of the gate insulating film and the surface area of the gate insulating film are determined such that the insulating ability of the gate insulating film is not degraded and the gate capacity is not increased. In this way, the size of the gate insulating film cannot be reduced in the conventional integrated circuit device. Thus, it has been considered that the potential of the channel region in the MISFET must be reduced in order to make it

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